



#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON) max</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	$52mΩ @V_{GS} = -4.5V$	SOT23	-5.0A
-200	100mΩ @V <sub>GS</sub> = -2.5V	30123	-3.6A

### **Description**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

### **Features**

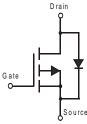
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

### **Mechanical Data**

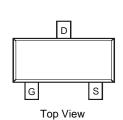
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
  Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)







Internal Schematic



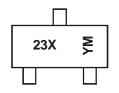
### **Ordering Information** (Note 4)

Pa	rt Number	Compliance	Case	Packaging
DM	G2305UX-7	Standard	SOT23	3000/Tape & Reel
DMC	S2305UX-13	Standard	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



23X = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note EVV	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	l <sub>D</sub>	-4.2 -3.3	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-5.0 -4.0	А
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-10	А	

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)	$P_{D}$	1.4	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	0	90	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	64	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>0</sub> JC	33	°C/W	
Operating and Storage Temperature Range	$T_{J_{I}}T_{STG}$	-55 to +150	°C	

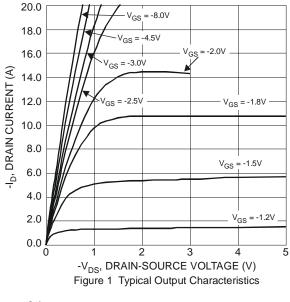
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

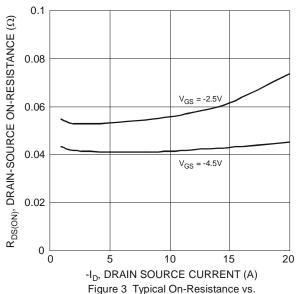
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	_		V	$V_{GS} = 0V, I_{D} = -250\mu A$		
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			40	52		$V_{GS} = -4.5V$ , $I_{D} = -4.2A$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	52	100	mΩ	$V_{GS} = -2.5V$ , $I_{D} = -3.4A$		
			68	200		$V_{GS} = -1.8V, I_D = -2A$		
Forward Transfer Admittance	Y <sub>fs</sub>	_	9	_	S	$V_{DS} = -5V, I_{D} = -4A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	_	808	_	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V -f = 1.0MHz		
Output Capacitance	Coss	_	85	_	pF			
Reverse Transfer Capacitance	Crss	_	77	_	pF	1 = 1.0WH IZ		
Gate Resistance	Rg		15.2		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$		
SWITCHING CHARACTERISTICS (Note 8)								
Total Gate Charge	$Q_g$	_	10.2	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		
Gate-Source Charge	$Q_{gs}$	_	1.3	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$ $-I_{D} = -3.5A$		
Gate-Drain Charge	$Q_{gd}$	_	2.2	_	nC	ID = -3.5A		
Turn-On Delay Time	t <sub>D(on)</sub>	_	10.8	_	ns			
Turn-On Rise Time	t <sub>r</sub>		13.7		ns	$V_{DS} = -4V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	79.3	_	ns	$R_G = 6\Omega$ , $I_D = -1A$		
Turn-Off Fall Time	t <sub>f</sub>	_	34.7	_	ns	<u> </u>		

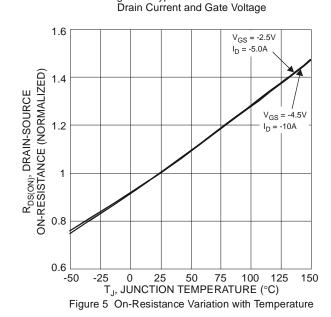
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

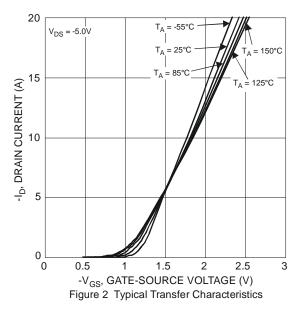
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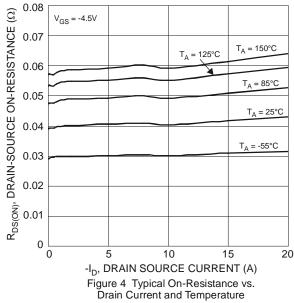


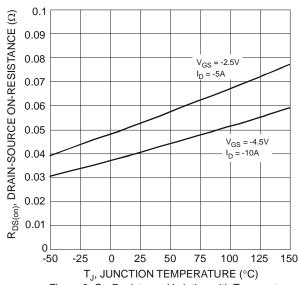














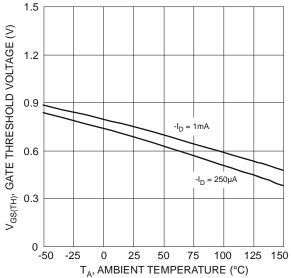
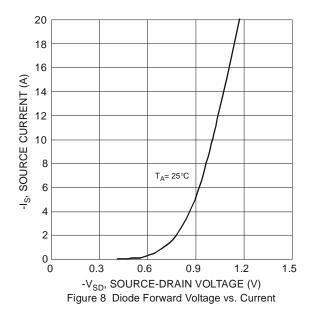
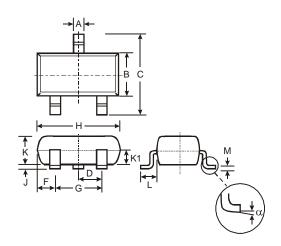


Figure 7 Gate Threshold Variation vs. Ambient Temperature



## **Package Outline Dimensions**

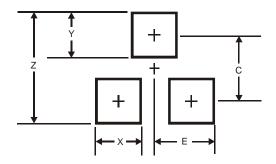
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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